

20 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor Rev. 01 — 18 May 2010

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

NPN low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

PNP complement: PBSS5620PA.

### 1.2 Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

### 1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

### 1.4 Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	20	V
I <sub>C</sub>	collector current		-	-	6	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 ms$	-	-	7	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 6 A; I <sub>B</sub> = 300 mA	<u>[1]</u> -	33	46	mΩ

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ .



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### 2. Pinning information

Table 2.	Pinning	
Pin	Description	Simplified outline Graphic symbol
1	base	
2	emitter	3
3	collector	
		1 2 sym021
		Transparent top view

### 3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
PBSS4620PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; three terminals; body 2 $\times$ 2 $\times$ 0.65 mm	SOT1061	

### 4. Marking

Table 4.	Marking codes	
Type num	iber	Marking code
PBSS462	0PA	A6

### 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	20	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	20	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	6	А
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	7	А
I <sub>B</sub>	base current		-	600	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	500	mW
			[2] _	1	W
			<u>[3]</u> _	1.4	W
			[4] _	2.1	W

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#### Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

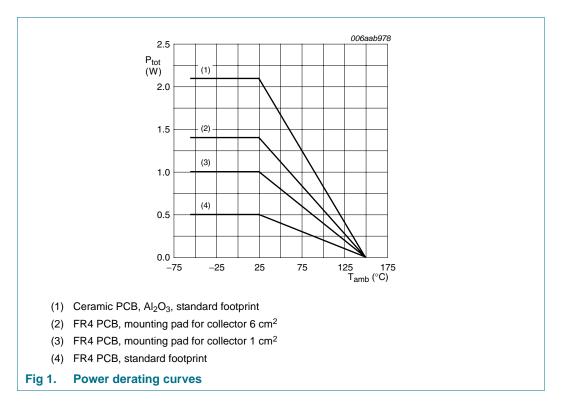
Symbol	Parameter	Conditions	Min	Max	Unit
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.



### 6. Thermal characteristics

Thermal characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
thermal resistance from	in free air	<u>[1]</u> _	-	250	K/W
junction to ambient		[2] _	-	125	K/W
		[3]	-	90	K/W
		[4]	-	60	K/W
	Parameter	ParameterConditionsthermal resistance fromin free air	ParameterConditionsMinthermal resistance from junction to ambientin free air[1]-[2]-[3]-	ParameterConditionsMinTypthermal resistance from junction to ambientin free air[1][2][3]	ParameterConditionsMinTypMaxthermal resistance from junction to ambientin free air[1]250[2]125[3]90

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

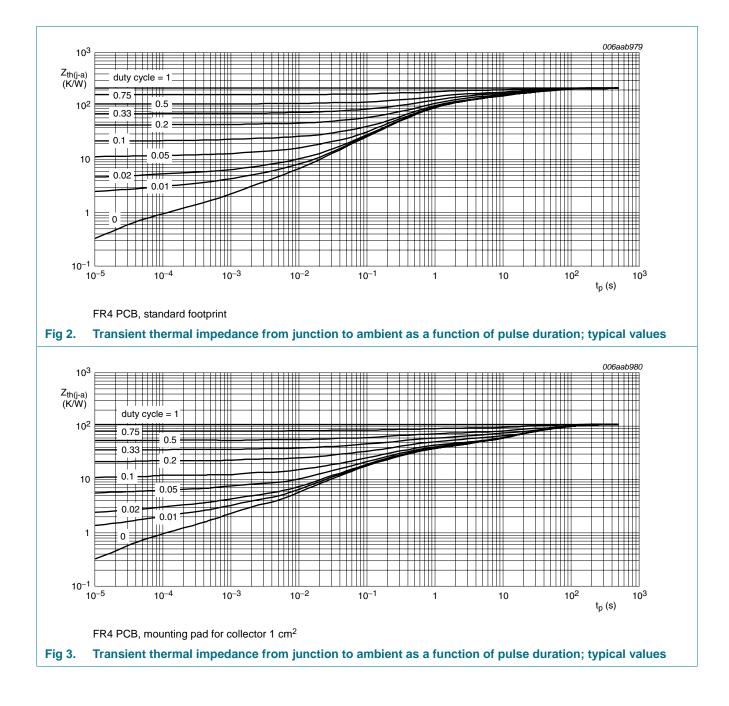
[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.

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## PBSS4620PA

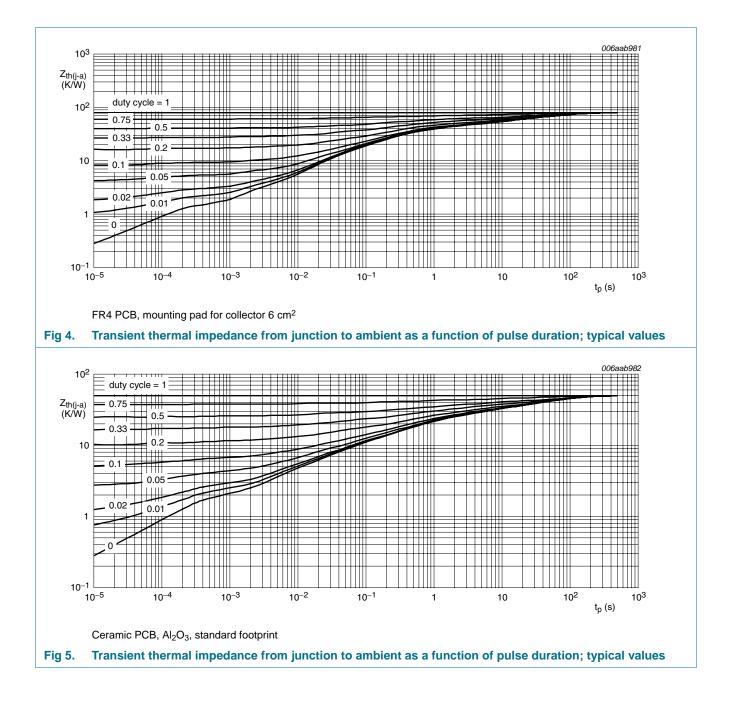
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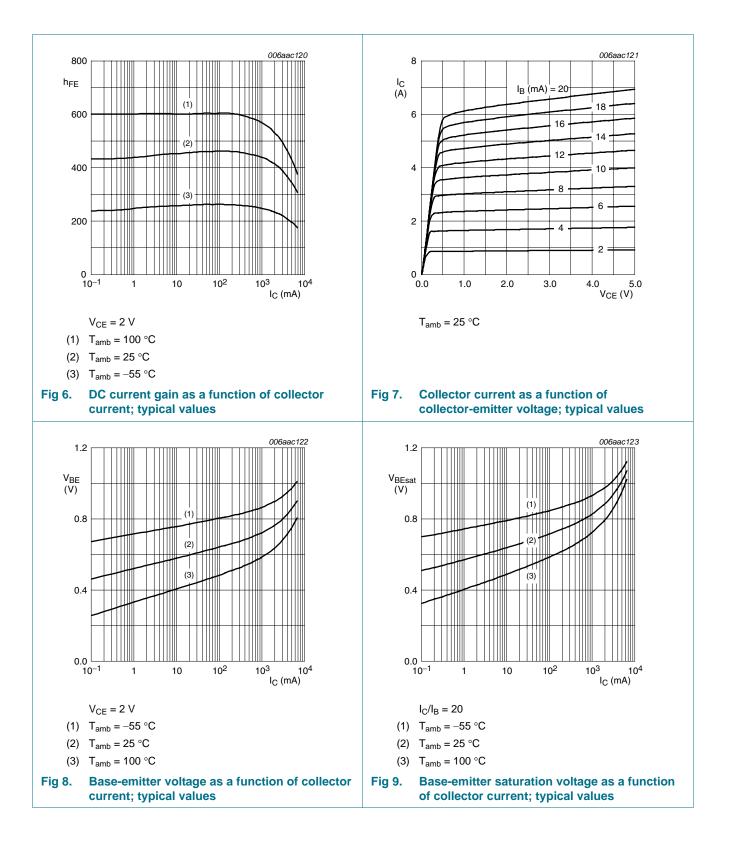
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### 7. Characteristics

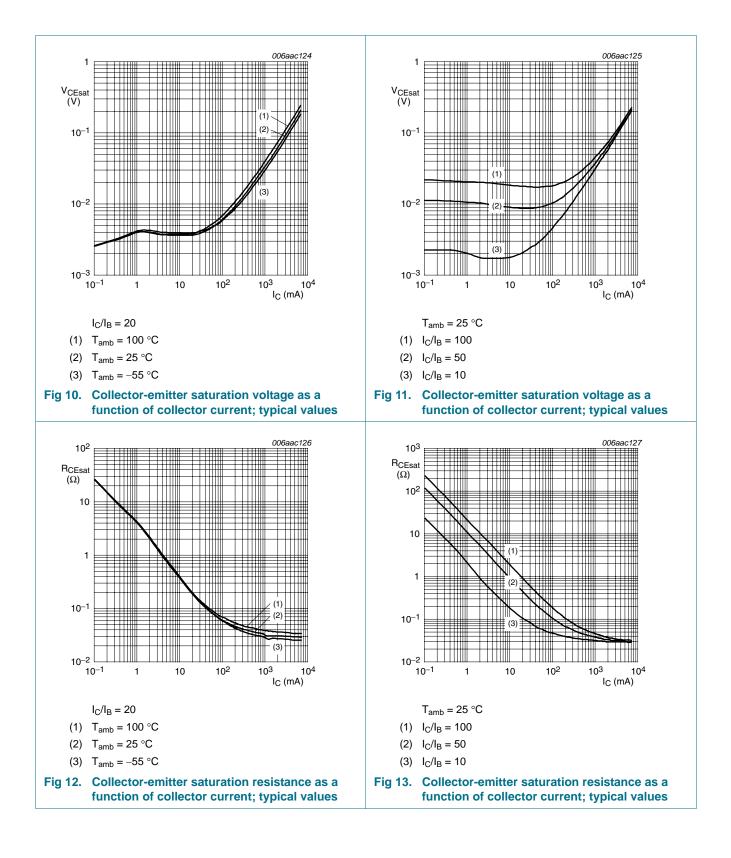
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = 16 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
	cut-off current	$V_{CB} = 16 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE} = 16 \text{ V}; \text{ V}_{BE} = 0 \text{ V}$	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = 2 V$	[1]			
		I <sub>C</sub> = 0.5 A	280	440	-	
		I <sub>C</sub> = 1 A	270	430	-	
		I <sub>C</sub> = 2 A	260	415	-	
		I <sub>C</sub> = 6 A	200	330	-	
V <sub>CEsat</sub>	collector-emitter	$I_{C} = 0.5 \text{ A}; I_{B} = 50 \text{ mA}$	<u>[1]</u> -	20	30	mV
	saturation voltage	$I_{C} = 1 \text{ A}; I_{B} = 50 \text{ mA}$	<u>[1]</u> -	37	55	mV
		$I_{C} = 1 \text{ A}; I_{B} = 10 \text{ mA}$	<u>[1]</u> -	50	70	mV
		$I_{C} = 2 \text{ A}; I_{B} = 20 \text{ mA}$	<u>[1]</u> -	85	120	mV
		$I_{C} = 3 \text{ A}; I_{B} = 30 \text{ mA}$	<u>[1]</u> -	120	170	mV
		$I_{C} = 4 \text{ A}; I_{B} = 400 \text{ mA}$	<u>[1]</u> -	135	185	mV
		$I_{C} = 6 \text{ A}; I_{B} = 300 \text{ mA}$	<u>[1]</u> -	200	275	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = 6 A; I <sub>B</sub> = 300 mA	<u>[1]</u> -	33	46	mΩ
V <sub>BEsat</sub>	base-emitter	I <sub>C</sub> = 1 A; I <sub>B</sub> = 10 mA	<u>[1]</u> -	0.75	0.9	V
	saturation voltage	$I_{C} = 6 \text{ A}; I_{B} = 300 \text{ mA}$	<u>[1]</u> -	0.97	1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 2 \text{ A}$	<u>[1]</u> -	0.74	0.9	V
t <sub>d</sub>	delay time	$V_{CC} = 9 V; I_C = 2 A;$	-	25	-	ns
t <sub>r</sub>	rise time	I <sub>Bon</sub> = 0.1 A; I <sub>Boff</sub> = -0.1 A	-	55	-	ns
t <sub>on</sub>	turn-on time	Boff0.1 A	-	80	-	ns
t <sub>s</sub>	storage time		-	285	-	ns
t <sub>f</sub>	fall time		-	50	-	ns
t <sub>off</sub>	turn-off time		-	335	-	ns
f⊤	transition frequency	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 100 mA; f = 100 MHz	50	80	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	80	95	pF

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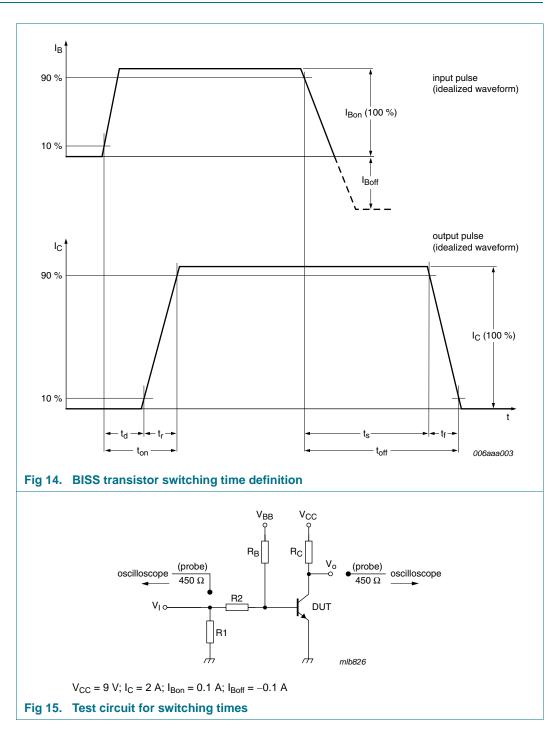


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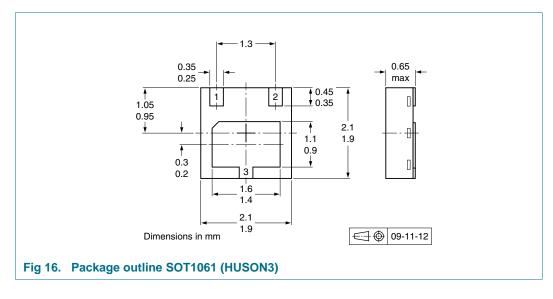
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### 8. Test information



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### 9. Package outline



### **10. Packing information**

#### Table 8. Packing methods

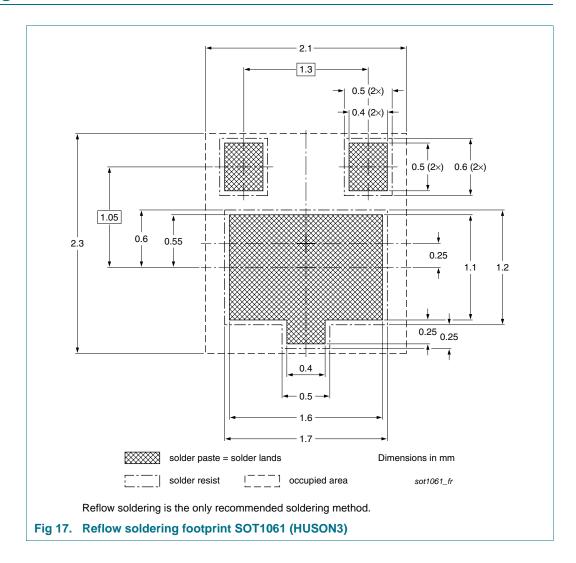
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PBSS4620PA	SOT1061	4 mm pitch, 8 mm tape and reel	-115

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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### **11. Soldering**



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### **12. Revision history**

Table 9. Revision hist	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
PBSS4620PA v.1	20100518	Product data sheet	-	-	

#### 20 V, 6 A NPN low V<sub>CEsat</sub> (BISS) transistor

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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